

# Ching-Hwa Ho

## List of Publications by Year in descending order

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191  
papers

6,406  
citations

66315

42  
h-index

79644

73  
g-index

191  
all docs

191  
docs citations

191  
times ranked

6810  
citing authors

#	ARTICLE	IF	CITATIONS
1	An all two-dimensional vertical heterostructure graphene/CuInP <sub>2</sub> S <sub>6</sub> /MoS <sub>2</sub> for negative capacitance field effect transistor. <i>Nanotechnology</i> , 2022, 33, 125703.	1.3	11
2	Internal Built-In Electric Fields at Organic-Inorganic Interfaces of Two-Dimensional Ruddlesden-Popper Perovskite Single Crystals. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 19818-19825.	4.0	3
3	Formation of van der Waals Stacked p-n Homojunction Optoelectronic Device of Multilayered ReSe <sub>2</sub> by Cr Doping. <i>Advanced Optical Materials</i> , 2022, 10, .	3.6	8
4	Molybdenum disulfide homogeneous junction diode fabrication and rectification characteristics. <i>Japanese Journal of Applied Physics</i> , 2022, 61, 086504.	0.8	1
5	Van der Waals Heterostructure Photodetectors with Bias-Selectable Infrared Photoresponses. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 32665-32674.	4.0	18
6	Dual phase two-color emission observed in van der Waals GaTe planes. <i>Applied Surface Science</i> , 2021, 542, 148593.	3.1	14
7	The Study of Optical Properties of III-VI Defect Semiconductor Group Compounds Ga <sub>2</sub> S <sub>3</sub> , Ga <sub>2</sub> Se <sub>3</sub> , In <sub>2</sub> S <sub>3</sub> , and In <sub>2</sub> Se <sub>3</sub> . <i>Advanced Photonics Research</i> , 2021, 2, 2000110.	1.7	8
8	Investigations of Electron-Electron and Interlayer Electron-Phonon Coupling in van der Waals hBN/WSe <sub>2</sub> /hBN Heterostructures by Photoluminescence Excitation Experiments. <i>Materials</i> , 2021, 14, 399.	1.3	8
9	The band-edge excitons observed in few-layer NiPS <sub>3</sub> . <i>Npj 2D Materials and Applications</i> , 2021, 5, .	3.9	21
10	Carrier-capture-assisted optoelectronics based on van der Waals materials to imitate medicine-acting metaplasticity. <i>Npj 2D Materials and Applications</i> , 2021, 5, .	3.9	7
11	Photoactive Electro-Controlled Visual Perception Memory for Emulating Synaptic Metaplasticity and Hebbian Learning. <i>Advanced Functional Materials</i> , 2021, 31, 2105345.	7.8	18
12	Thermoreflectance characterization of the band-edge excitons observed in multilayered CuInP <sub>2</sub> S <sub>6</sub> . <i>FlatChem</i> , 2021, 29, 100290.	2.8	8
13	Probing negatively charged and neutral excitons in MoS <sub>2</sub> /hBN and hBN/MoS <sub>2</sub> /hBN van der Waals heterostructures. <i>Nanotechnology</i> , 2021, 32, 145717.	1.3	17
14	Upconversion of Light into Bright Intravalley Excitons via Dark Intervalley Excitons in hBN-Encapsulated WSe <sub>2</sub> Monolayers. <i>ACS Nano</i> , 2021, 15, 19165-19174.	7.3	18
15	Nanowire Grid Polarization and Polarized Excitonic Emission Observed in Multilayer GaTe. <i>Journal of Physical Chemistry Letters</i> , 2020, 11, 608-617.	2.1	20
16	Multilayer GaSe/InSe Heterointerface-Based Devices for Charge Transport and Optoelectronics. <i>ACS Applied Nano Materials</i> , 2020, 3, 11769-11776.	2.4	18
17	Ga <sub>2</sub> Se <sub>3</sub> Defect Semiconductors: The Study of Direct Band Edge and Optical Properties. <i>ACS Omega</i> , 2020, 5, 18527-18534.	1.6	14
18	Inverse paired-pulse facilitation in neuroplasticity based on interface-boosted charge trapping layered electronics. <i>Nano Energy</i> , 2020, 77, 105258.	8.2	22

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19	Tuning Interface Barrier in 2D BP/ReSe <sub>2</sub> Heterojunctions in Control of Optoelectronic Performances and Energy Conversion Efficiencies. ACS Photonics, 2020, 7, 2886-2895.	3.2	20
20	Oxidation-boosted charge trapping in ultra-sensitive van der Waals materials for artificial synaptic features. Nature Communications, 2020, 11, 2972.	5.8	83
21	Optical and Thermoelectric Properties of Surface-Oxidation Sensitive Layered Zirconium Dichalcogenides ZrS <sub>2</sub> xSex (x = 0, 1, 2) Crystals Grown by Chemical Vapor Transport. Crystals, 2020, 10, 327.	1.0	18
22	Study of Structural, Thermoelectric, and Photoelectric Properties of Layered Tin Monochalcogenides SnX (X = S, Se) for Energy Application. ACS Applied Energy Materials, 2020, 3, 4896-4905.	2.5	22
23	High-responsivity broad-band sensing and photoconduction mechanism in direct-Gap In <sub>2</sub> Se <sub>3</sub> nanosheet photodetectors. Nanotechnology, 2020, 31, 465201.	1.3	23
24	Photoluminescence and time-resolved photoluminescence study of GaSe <sub>1-x</sub> S <sub>x</sub> mixed crystal. , 2020, , .		0
25	Temperature-dependent ultraviolet photoluminescence in hierarchical Zn, ZnO and ZnO/Zn nanostructures. Nanoscale, 2019, 11, 13385-13396.	2.8	32
26	Mode-locked Tm-doped fiber laser with large modulation depth ReS <sub>1.02</sub> Se <sub>0.98</sub> nanosheet saturable absorber. Japanese Journal of Applied Physics, 2019, 58, 100907.	0.8	5
27	High-Mobility InSe Transistors: The Nature of Charge Transport. ACS Applied Materials & Interfaces, 2019, 11, 35969-35976.	4.0	23
28	Multifunctional full-visible-spectrum optoelectronics based on a van der Waals heterostructure. Nano Energy, 2019, 66, 104107.	8.2	28
29	InSe Tribotronic Transistors: Low Voltage Operational, Low Power Consuming, and High Sensitive Tactile Switch Based on 2D Layered InSe Tribotronics (Adv. Funct. Mater. 19/2019). Advanced Functional Materials, 2019, 29, 1970125.	7.8	0
30	Few-layer ReS <sub>2</sub> (1-x)Se <sub>2x</sub> nanoflakes for noise-like pulse generation in a mode-locked ytterbium-doped fiber laser. Journal of Materials Chemistry C, 2019, 7, 6900-6904.	2.7	19
31	Analog Circuit Applications Based on All 2D Ambipolar ReSe <sub>2</sub> Field Effect Transistors. Advanced Functional Materials, 2019, 29, 1809011.	7.8	36
32	Low Voltage Operational, Low Power Consuming, and High Sensitive Tactile Switch Based on 2D Layered InSe Tribotronics. Advanced Functional Materials, 2019, 29, 1809119.	7.8	28
33	Effect of Cr on the Structure and Property of Mo <sub>1-x</sub> Cr <sub>x</sub> Se <sub>2</sub> (0 ≤ x ≤ 0.2) and Cr <sub>2</sub> Se <sub>3</sub> . ACS Applied Electronic Materials, 2019, 1, 370-378.	2.0	12
34	Complete-series excitonic dipole emissions in few layer ReS <sub>2</sub> and ReSe <sub>2</sub> observed by polarized photoluminescence spectroscopy. Nano Energy, 2019, 56, 641-650.	8.2	49
35	Synthesis, optical characterization, and environmental applications of In <sup>2+</sup> -Ga <sub>2</sub> O <sub>3</sub> nanowires. , 2019, , 67-90.		8
36	Ternary ReS <sub>2</sub> (1-x)Se <sub>2x</sub> alloy saturable absorber for passively Q-switched and mode-locked erbium-doped all-fiber lasers. Photonics Research, 2019, 7, 283.	3.4	26

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37	Ultraefficient Ultraviolet and Visible Light Sensing and Ohmic Contacts in High-Mobility InSe Nanoflake Photodetectors Fabricated by the Focused Ion Beam Technique. ACS Applied Materials & Interfaces, 2018, 10, 5740-5749.	4.0	45
38	Curvature-dependent flexible light emission from layered gallium selenide crystals. RSC Advances, 2018, 8, 2733-2739.	1.7	21
39	Temperature dependence of direct and indirect band gaps of Bi <sub>13</sub> Te <sub>18</sub> hexagonal rod crystals. Materials Chemistry and Physics, 2018, 206, 71-75.	2.0	8
40	Polarization Photoelectric Conversion in Layered GeS. Advanced Optical Materials, 2018, 6, 1701194.	3.6	36
41	High Mobilities in Layered InSe Transistors with Indium-Encapsulation-Induced Surface Charge Doping. Advanced Materials, 2018, 30, e1803690.	11.1	101
42	Dynamic tungsten diselenide nanomaterials: supramolecular assembly-induced structural transition over exfoliated two-dimensional nanosheets. Chemical Science, 2018, 9, 5452-5460.	3.7	22
43	In-Plane Axially Enhanced Photocatalysis by Re <sub>4</sub> Diamond Chains in Layered ReS <sub>2</sub> . Journal of Physical Chemistry C, 2018, 122, 18776-18784.	1.5	14
44	The Study of Near-Band-Edge Property in Oxygen-Incorporated ZnS for Acting as an Efficient Crystal Photocatalyst. ACS Omega, 2018, 3, 6351-6359.	1.6	8
45	Bending photoluminescence study of 2D layered GaSe. , 2018, , .		0
46	Anisotropic Spectroscopy and Electrical Properties of 2D ReS <sub>2</sub> (1-x)Se <sub>2</sub> (x) Alloys with Distorted 1T Structure. Small, 2017, 13, 1603788.	5.2	70
47	The structure and optoelectronic properties of a new (Bi <sub>2</sub> S <sub>3</sub> ) <sub>9</sub> (Te <sub>3</sub> ) <sub>2/3</sub> hexagonal nano-/micro-rod. Chemical Communications, 2017, 53, 3741-3744.	2.2	14
48	The study of flexible emission and photoconductivity in 2D layered InSe toward an applicable 1000-nm light emitter and absorber. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	1.1	9
49	Direct and indirect light emissions from layered ReS <sub>2</sub> (1-x)Se <sub>2</sub> (x) (0 ≤ x ≤ 1) Te <sub>3</sub> ETQq1 1.0,784314 rgBT / O <sub>1.3</sub> 19		
50	Direct identification of monolayer rhenium diselenide by an individual diffraction pattern. Nano Research, 2017, 10, 2535-2544.	5.8	5
51	Pressure-induced metallization and superconducting phase in ReS <sub>2</sub> . Npj Quantum Materials, 2017, 2, .	1.8	53
52	Interplay Between Cr Dopants and Vacancy Clustering in the Structural and Optical Properties of WSe <sub>2</sub> . ACS Nano, 2017, 11, 11162-11168.	7.3	33
53	Cleavage tendency of anisotropic two-dimensional materials: $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"} \rangle \langle \text{mml:mrow} \langle \text{mml:mi} \text{Re} \langle \text{mml:mi} \langle \text{mml:msub} \langle \text{mml:mi} \rangle \langle \text{mml:mi} \rangle \langle \text{mml:mi} \rangle \langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"} \rangle \langle \text{mml:mi} \text{Physical Review B, 2017, 96, .$	1.1	36
54	Optical Study of High Quality <i>x</i> -ZnS Crystals for UV Photodiodes and Photoelectrochemical Applications. ChemistrySelect, 2017, 2, 9391-9395.	0.7	2

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55	Synthesis and Optical Characterization of Oxygen-Incorporated ZnS <sub>(1-x)</sub> O <sub>x</sub> for UV-Visible Color Palette Light-Emission Matter. ACS Omega, 2017, 2, 4514-4523.	1.6	15
56	High-Mobility InSe Transistors: The Role of Surface Oxides. ACS Nano, 2017, 11, 7362-7370.	7.3	177
57	Polarized Band-Edge Emission and Dichroic Optical Behavior in Thin Multilayer GeS. Advanced Optical Materials, 2017, 5, 1600814.	3.6	45
58	Optical and photodetector properties of stripe-like InS crystal. RSC Advances, 2016, 6, 97445-97448.	1.7	8
59	Synthesis of In <sub>2</sub> S <sub>3</sub> and Ga <sub>2</sub> S <sub>3</sub> crystals for oxygen sensing and UV photodetection. Sensors and Actuators A: Physical, 2016, 245, 119-126.	2.0	49
60	Synthesis and optical characterization of a high-quality ZnS substrate for optoelectronics and UV solar-energy conversion. RSC Advances, 2016, 6, 81053-81059.	1.7	4
61	Optical Characterization of Structural Quality in the Formation of In <sub>2</sub> O <sub>3</sub> Thin-Film Nanostructures. Journal of Physical Chemistry C, 2016, 120, 21983-21989.	1.5	16
62	Disorder engineering and conductivity dome in ReS <sub>2</sub> with electrolyte gating. Nature Communications, 2016, 7, 12391.	5.8	109
63	Thickness-dependent carrier transport and optically enhanced transconductance gain in III-VI multilayer InSe. 2D Materials, 2016, 3, 025019.	2.0	56
64	Observation of near-band-edge photoluminescence and UV photoresponse in near-stoichiometric Zn <sub>2</sub> SnO <sub>4</sub> nanowires. Materials Research Express, 2016, 3, 066201.	0.8	4
65	2D multilayer InSe – An applicable 1000 nm light emitter and absorber. , 2016, , .		2
66	Optical Characterization of Strong UV Luminescence Emitted from the Excitonic Edge of Nickel Oxide Nanotowers. Scientific Reports, 2015, 5, 15856.	1.6	20
67	Bending Photoluminescence and Surface Photovoltaic Effect on Multilayer InSe 2D Microplate Crystals. Advanced Optical Materials, 2015, 3, 1750-1758.	3.6	75
68	Amorphous effect on the advancing of structural-phase transition in $\text{In}_2\text{Se}_3$ polycrystalline layers. , 2015, , .		0
69	Optical-memory switching and oxygen detection based on the CVT grown $\hat{\Gamma}^3$ - and $\hat{\Gamma}^\pm$ -phase In <sub>2</sub> Se <sub>3</sub> . Sensors and Actuators B: Chemical, 2015, 209, 811-819.	4.0	15
70	Polarized optical sensing and band-edge transitions in Ag(In <sub>0.5</sub> Al <sub>0.5</sub> )S <sub>2</sub> . Applied Physics Express, 2015, 8, 025801.	1.1	1
71	Surface Sensing and Optical Behavior of Al-Based Silver Chalcopyrites. Journal of Electronic Materials, 2015, 44, 984-990.	1.0	0
72	Influence of rhenium on the structural and optical properties of molybdenum disulfide. Japanese Journal of Applied Physics, 2015, 54, 04DH05.	0.8	21

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73	Structural property and optical band edge of Ag(In <sub>0.5</sub> Al <sub>0.5</sub> )S <sub>2</sub> . Journal of Materials Science: Materials in Electronics, 2015, 26, 3766-3771.	1.1	0
74	Integrated digital inverters based on two-dimensional anisotropic ReS <sub>2</sub> field-effect transistors. Nature Communications, 2015, 6, 6991.	5.8	505
75	Single-Layer ReS <sub>2</sub> : Two-Dimensional Semiconductor with Tunable In-Plane Anisotropy. ACS Nano, 2015, 9, 11249-11257.	7.3	353
76	Optical behavior and structural property of CuAlS <sub>2</sub> and AgAlS <sub>2</sub> wide-bandgap chalcopyrites. Applied Optics, 2014, 53, E7.	0.9	10
77	Piezoreflectance study of near band edge excitonic-transitions of mixed-layered crystal Mo(SxSe <sub>1-x</sub> ) <sub>2</sub> solid solutions. Journal of Applied Physics, 2014, 115, .	1.1	20
78	Structural phase transition and erasable optically memorized effect in layered $\hat{I}^3$ -In <sub>2</sub> Se <sub>3</sub> crystals. Journal of Applied Physics, 2014, 115, .	1.1	20
79	Analyzing a steady-state phenomenon using an ensemble of sequential transient events: A proof of concept on photocurrent of bacteriorhodopsin upon continuous photoexcitation. Journal of Applied Physics, 2014, 116, 144701.	1.1	0
80	Transport properties in semiconducting NbS <sub>2</sub> nanoflakes. Applied Physics Letters, 2014, 105, .	1.5	39
81	Formation and stability of point defects in monolayer rhenium disulfide. Physical Review B, 2014, 89, .	1.1	151
82	Monolayer behaviour in bulk ReS <sub>2</sub> due to electronic and vibrational decoupling. Nature Communications, 2014, 5, 3252.	5.8	906
83	Large-area nanoscale farmland-like surfaces of one-dimensional NbO <sub>2</sub> nanorods with multi-growth directions: studies on the purple-blue photoluminescence and low-field electron emissions. Journal of Materials Chemistry C, 2014, 2, 8667-8672.	2.7	23
84	Amorphous effect on the advancing of wide-range absorption and structural-phase transition in $\hat{I}^3$ -In <sub>2</sub> Se <sub>3</sub> polycrystalline layers. Scientific Reports, 2014, 4, 4764.	1.6	38
85	Photoluminescence mechanisms of metallic Zn nanospheres, semiconducting ZnO nanoballoons and metal-semiconductor Zn/ZnO nanospheres. Scientific Reports, 2014, 4, 6967.	1.6	84
86	Optically decomposed near-band-edge structure and excitonic transitions in Ga <sub>2</sub> S <sub>3</sub> . Scientific Reports, 2014, 4, 6143.	1.6	52
87	Characterization of nitrogen doped p-type ZnO thin films prepared by reactive ion beam sputter deposition. Surface and Coatings Technology, 2013, 231, 492-495.	2.2	14
88	Direct vapor transport synthesis of ZnGa <sub>2</sub> O <sub>4</sub> nanowires with superior photocatalytic activity. Journal of Alloys and Compounds, 2013, 555, 325-329.	2.8	22
89	Thickness-tunable band gap modulation in $\hat{I}^3$ -In <sub>2</sub> Se <sub>3</sub> . RSC Advances, 2013, 3, 24896.	1.7	26
90	The study of optical band edge property of bismuth oxide nanowires $\hat{I}^{\pm}$ -Bi <sub>2</sub> O <sub>3</sub> . Optics Express, 2013, 21, 11965.	1.7	96

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91	Optical characterization of InAlAs/InGaAs metamorphic high-electron mobility transistor structures with tensile and compressive strain. <i>Thin Solid Films</i> , 2013, 529, 217-221.	0.8	2
92	Surface Oxide Effect on Optical Sensing and Photoelectric Conversion of $\text{In}_2\text{Se}_3$ Hexagonal Microplates. <i>ACS Applied Materials &amp; Interfaces</i> , 2013, 5, 2269-2277.	4.0	91
93	The study of rapid thermal annealing on arsenic-doped ZnO for the p-type ZnO formation. <i>Journal of Crystal Growth</i> , 2013, 362, 193-196.	0.7	10
94	NIR and UV enhanced photon detector made by diindium trichalcogenides. <i>Optical Materials Express</i> , 2013, 3, 1420.	1.6	15
95	Optical properties of wide-band-gap chalcopyrite $\text{CuAl}(\text{Se}_{0.5}\text{S}_{0.5})_2$ evaluated by thermoreflectance spectroscopy. <i>Optical Materials Express</i> , 2013, 3, 480.	1.6	5
96	Practical and User-Friendly Circuits and System Design for Signalsâ€™ Sensing and Generation. <i>Circuits and Systems</i> , 2013, 04, 387-392.	0.1	3
97	Dichroic Electro-Optical Behavior of Rhenium Sulfide Layered Crystal. <i>Crystal Structure Theory and Applications</i> , 2013, 02, 65-69.	0.3	10
98	Nitrogen Doping Effect on Optical Property of Gallium Oxide Nanowires. <i>ECS Journal of Solid State Science and Technology</i> , 2012, 1, P78-P81.	0.9	5
99	Surface sensing behavior and band edge properties of $\text{AgAlS}_2$ : Experimental observations in optical, chemical, and thermoreflectance spectroscopy. <i>AIP Advances</i> , 2012, 2, .	0.6	13
100	Optical characterization of band-edge property of $\text{In}_6\text{S}_7$ compound. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	20
101	Structural and Band-Edge Properties of $\text{Cu}(\text{Al}_x\text{In}_{1-x})\text{S}_2$ ( $0 \leq x \leq 1$ ) Series Chalcopyrite Semiconductors. <i>Solid State Phenomena</i> , 2012, 194, 133-138.	0.3	3
102	Room-temperature wide-range photoluminescence and semiconducting characteristics of two-dimensional pure metallic Zn nanoplates. <i>RSC Advances</i> , 2012, 2, 2123.	1.7	26
103	The study of below and above band-edge imperfection states in $\text{In}_2\text{S}_3$ solar energy materials. <i>Physica B: Condensed Matter</i> , 2012, 407, 3052-3055.	1.3	11
104	Cathodoluminescence and Field-Emission Properties of $\text{In}^{2+}\text{-Ga}_2\text{O}_3$ Nanobelts. <i>Journal of Electronic Materials</i> , 2012, 41, 3056-3061.	1.0	5
105	Influence of anionic substitution on the electrolyte electroreflectance study of band edge transitions in single crystal $\text{Cu}_2\text{ZnSn}(\text{S}_x\text{Se}_{1-x})_4$ solid solutions. <i>Optical Materials</i> , 2012, 34, 1362-1365.	1.7	57
106	Enhanced photoelectric-conversion yield in niobium-incorporated $\text{In}_2\text{S}_3$ with intermediate band. <i>Journal of Materials Chemistry</i> , 2011, 21, 10518.	6.7	57
107	Piezoreflectance and Raman Characterization of $\text{Mo}_x\text{W}_x\text{S}_2$ Layered Mixed Crystals. <i>Solid State Phenomena</i> , 2011, 170, 55-59.	0.3	8
108	Electronic structure and optical property of $\text{As}_2(\text{Te}_{1-x}\text{S})_3$ and $\text{As}_2(\text{Te}_{1-x}\text{Se})_3$ crystals. <i>Journal of Alloys and Compounds</i> , 2011, 509, 7198-7204.	2.8	6



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109	Direct Optical Observation of Band-Edge Excitons, Band Gap, and Fermi Level in Degenerate Semiconducting Oxide Nanowires $\text{In}_2\text{O}_3$ . Journal of Physical Chemistry C, 2011, 115, 25088-25096.	1.5	58
110	Enhanced Photocatalytic Activity in $\text{In}_2\text{O}_3$ Nanobelts. Journal of the American Ceramic Society, 2011, 94, 3117-3122.	1.9	63
111	Synthesis of $\text{In}_2\text{O}_3$ nanowires as a broadband emitter. Applied Physics A: Materials Science and Processing, 2011, 102, 105-108.	1.1	11
112	Single crystal growth and characterization of copper aluminum indium disulfide chalcopyrites. Journal of Crystal Growth, 2011, 317, 52-59.	0.7	10
113	Temperature Dependent Crystal-Field Splitting and Band-Edge Characteristic in $\text{Cu}(\text{Al}_x\text{In}_{1-x})\text{S}_2$ Series Solar Energy Materials. Journal of the Electrochemical Society, 2011, 158, H554.	1.3	8
114	Optical Characterization of Electronic Structure of $\text{CuInS}_2$ and $\text{CuAlS}_2$ Chalcopyrite Crystals. Solid State Phenomena, 2011, 170, 21-24.	0.3	1
115	Effect of temperature on lateral growth of ZnO grains grown by MOCVD. Ceramics International, 2010, 36, 69-73.	2.3	38
116	Growth and characterization of near-band-edge transitions in $\text{In}_2\text{S}_3$ single crystals. Journal of Crystal Growth, 2010, 312, 2718-2723.	0.7	52
117	Nitrogen-doped ZnO prepared by capillaritron reactive ion beam sputtering deposition. Applied Surface Science, 2010, 256, 4153-4156.	3.1	5
118	Thermoreflectance characterization of band-edge excitonic transitions in $\text{CuAlS}_2$ ultraviolet solar-cell material. Applied Physics Letters, 2010, 96, .	1.5	23
119	The study of surface photoconductive response in indium sulfide crystals. Journal Physics D: Applied Physics, 2010, 43, 415301.	1.3	17
120	Temperature-dependent photoconductivity in $\text{In}_2\text{S}_3$ single crystals. Journal of Applied Physics, 2010, 108, .	1.1	29
121	Polarized-thermoreflectance study of the band-edge transitions in $\text{Cu}(\text{Al}_{0.05}\text{In}_{0.05})\text{S}_2$ solar-energy related crystal. Optics Express, 2010, 18, 3820.	1.7	9
122	Thermoreflectance characterization of $\text{In}_2\text{O}_3$ thin-film nanostrips. Optics Express, 2010, 18, 16360.	1.7	57
123	Electronic Structure and $E_{[1]}$ Excitons of $\text{CuInS}_2$ Energy-Related Crystals Studied by Temperature-Dependent Thermoreflectance Spectroscopy. Journal of the Electrochemical Society, 2010, 157, H219.	1.3	11
124	Structural and luminescent property of gallium chalcogenides $\text{GaSe}_{1-x}\text{S}_x$ layer compounds. Journal of Materials Science: Materials in Electronics, 2009, 20, 207-210.	1.1	9
125	In-plane anisotropic electrical and optical properties of gold-doped rhenium disulphide. Journal of Materials Science: Materials in Electronics, 2009, 20, 476-479.	1.1	7
126	Optical and electrical characteristics of GaAs/InGaAs quantum-well device. Journal of Alloys and Compounds, 2009, 471, 567-569.	2.8	9



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127	Optical anisotropy of Au-doped ReS <sub>2</sub> crystals. Journal of Alloys and Compounds, 2009, 480, 94-96.	2.8	16
128	Optical anisotropy of near band-edge transitions in zinc oxide nanostructures. Journal of Alloys and Compounds, 2009, 480, 50-53.	2.8	5
129	Thermoelectric properties of ZnS-Sb alloys doped with In. Journal of Alloys and Compounds, 2009, 480, 73-75.	2.8	21
130	Optical investigation of band-edge structure and built-in electric field of AlGaIn/GaN heterostructures by means of thermoreflectance, photoluminescence, and contactless electroreflectance spectroscopy. Optics Letters, 2009, 34, 3604.	1.7	9
131	High room-temperature photoluminescence of one-dimensional Ta <sub>2</sub> O <sub>5</sub> nanorod arrays. Nanotechnology, 2009, 20, 445708.	1.3	59
132	Temperature-dependent photoreflectance and photoluminescence characterization of the subband structure and built-in electric field of GaAs/GaInAs graded-channel high electron mobility transistor structures. Semiconductor Science and Technology, 2009, 24, 035013.	1.0	3
133	Optical properties of near band-edge transitions in well-aligned and tilted ZnO nanostructures. Journal Physics D: Applied Physics, 2008, 41, 165410.	1.3	4
134	Characterization of indirect and direct interband transitions of anatase TiO <sub>2</sub> by thermoreflectance spectroscopy. Applied Physics Letters, 2008, 93, .	1.5	40
135	Compensation and Carrier Conduction in Synthetic Fe <sub>1-x</sub> Ni <sub>x</sub> S <sub>2</sub> (0 ≤ x ≤ 0.1) Single Crystals. Journal of the Electrochemical Society, 2008, 155, H254.	1.3	2
136	Band-edge properties of layered germanium dichalcogenides. Physical Review B, 2007, 76, .	1.1	2
137	Comprehensive Characterization of AlGaAs-InGaAs-GaAs Composite-Channel High-Electron Mobility Transistor. Journal of the Electrochemical Society, 2007, 154, H951.	1.3	13
138	Optical anisotropy of ZnO nanocrystals on sapphire by thermoreflectance spectroscopy. Optics Letters, 2007, 32, 2765.	1.7	12
139	Optical characterization of a GaAs/In <sub>0.5</sub> (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>0.5</sub> P/GaAs heterostructure cavity by piezoreflectance spectroscopy. Optics Express, 2007, 15, 13886.	1.7	5
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